

Reflective Mask Blank

ABSTRACT

5 A reflective mask blank including a substrate, a multilayer reflection film that is
formed on the substrate and reflects exposure light, a protection film that is formed on the
multilayer reflection film, and an absorber film that is formed in contact with the protection
film and absorbs the exposure light is provided. The reflective mask blank is a material
for a reflective mask used in EUV lithography using EUV light as the exposure light. The
10 absorber film includes a main region that occupies not less than 94 % of a thickness of the
absorber film, the main region consists of tantalum and nitrogen and is constituted of
multiple layers that include at least one low nitrogen content layer having a nitrogen
content of not more than 20 at%, and at least one high nitrogen content layer having a
nitrogen content of 40 at% to 60 at%.

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[Figure 1]